IN THE CLAIMS

Please cancel claims 1-10, and in place thereof substitute new claims 11-20 as follows:

--11. A method for removing a deposited film inside a chamber which comprises:

providing a hot element in the chamber, the hot element having at least a surface which comprises platinum;

exhausting said chamber;

heating the hot element;

supplying a cleaning gas into the chamber;

contacting the cleaning gas with the heated hot element to decompose and/or activate the cleaning gas and generate an activated species therefrom;

allowing the activated species to convert the deposited film into a gaseous substance; and

removing the gaseous substance from the chamber.- -

--12. The method according to claim 11, wherein said chamber comprises a CVD apparatus and the method further comprises:

heating the hot element;

supplying a material gas to the chamber;

contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and

forming the deposited film which comprises at least one element from said material gas on a substrate.- -

--13. The method according to claim 11, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.- -

--14. The method according to claim 12, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.- -

- -15. The method according to claim 11, wherein said cleaning gas is a gas containing at least one of fluorine (F_2), chlorine (Cl_2), nitrogen trifluoride (NF_3), carbon tetrafluoride (CF_4), hexafluoroethane (C_2F_6), octafluoropropane (C_3F_8), carbon tetrachloride (CCl_4), pentafluorochloroethane (C_2ClF_5), trifluorochlorine (ClF_3), trifluorochloromethane ($CClF_3$), and sulfur hexafluoride (SF_6), and mixtures thereof- -

- -16. The method according to claim 12, wherein said cleaning gas is a gas containing at least one of fluorine (F_2), chlorine (Cl_2), nitrogen trifluoride (NF_3), carbon tetrafluoride (CF_4), hexafluoroethane (C_2F_6), octafluoropropane (C_3F_8), carbon tetrachloride (CCl_4), pentafluorochloroethane (C_2ClF_5), trifluorochlorine (ClF_3), trifluorochloromethane ($CClF_3$), sulfur hexafluoride (SF_6), and mixtures thereof.- -

- -17. A CVD apparatus comprising:

a chamber having a material gas inlet and a cleaning gas inlet;

a hot element located in the chamber, the hot element having a surface which comprises platinum;

means for exhausting the chamber;

a source of material gas coupled to the material gas inlet;

means for heating the hot element to a first temperature sufficient to decompose and/or activate the material gas:

a source of cleaning gas coupled to the cleaning gas inlet; and

means for heating the hot element to a second temperature sufficient to decompose and/or activate the cleaning gas to generate an activated species therefrom which active species is able to convert a film deposited inside said chamber to gaseous substance, which gaseous substance can be removed from the chamber by exhausting the chamber.- -

- -18. The CVD apparatus according to claim 17, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.- -